

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)



ON Semiconductor®

<http://onsemi.com>

Complementary Power Transistors

DPAK For Surface Mount Applications

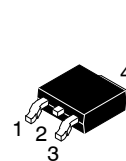
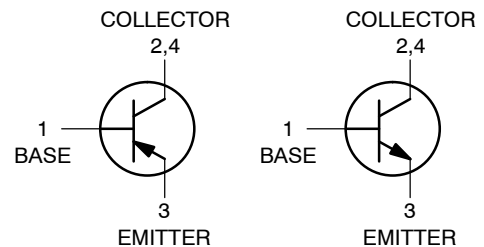
Designed for general purpose amplifier and low speed switching applications.

Features

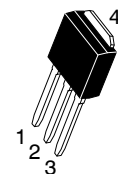
- Lead Formed for Surface Mount Applications in Plastic Sleeves
- Straight Lead Version in Plastic Sleeves ("1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series
- Epoxy Meets UL 94, V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

**SILICON
POWER TRANSISTORS
3 AMPERES
40 AND 100 VOLTS
15 WATTS**

COMPLEMENTARY



**DPAK
CASE 369C
STYLE 1**

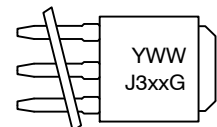


**IPAK
CASE 369D
STYLE 1**

MARKING DIAGRAMS



DPAK



IPAK

A = Site Code
Y = Year
WW = Work Week
xx = 1, 1C, 2, or 2C
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	V_{CEO}	40 100	Vdc
Collector–Base Voltage MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	V_{CB}	40 100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous	I_C	3.0	Adc
Collector Current – Peak	I_{CM}	5.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.56 0.012	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	8.3	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Ambient*	$R_{\theta JA}$	80	$^\circ\text{C}/\text{W}$
Lead Temperature for Soldering Purposes	T_L	260	$^\circ\text{C}$

*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 30\text{ mAdc}$, $I_B = 0$) MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	$V_{CEO(sus)}$	40 100	– –	Vdc
Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G	I_{CEO}	– –	50 50	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{EB} = 0$)	ICES	–	20	μAdc
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	1	mAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 1\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$) ($I_C = 3\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$)	h_{FE}	25 10	– 50	
Collector–Emitter Saturation Voltage ($I_C = 3\text{ Adc}$, $I_B = 375\text{ mAdc}$)	$V_{CE(sat)}$	–	1.2	Vdc
Base–Emitter On Voltage ($I_C = 3\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$)	$V_{BE(on)}$	–	1.8	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product (Note 2) ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1\text{ MHz}$)	f_T	3	–	MHz
Small–Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ kHz}$)	h_{fe}	20	–	

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS

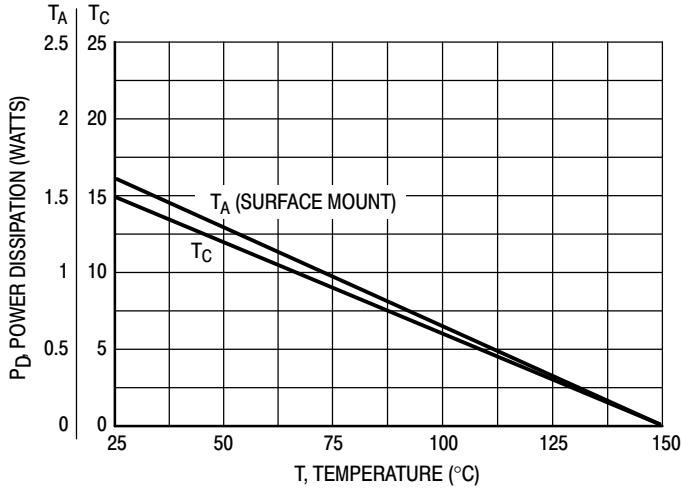
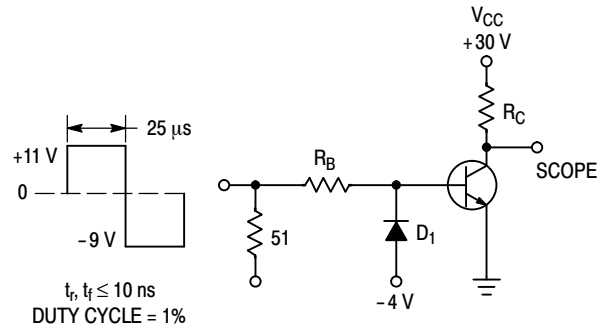


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
 D_1 MUST BE FAST RECOVERY TYPE, e.g.:
 1N5825 USED ABOVE $I_B \approx 100$ mA
 MSD6100 USED BELOW $I_B \approx 100$ mA
 REVERSE ALL POLARITIES FOR PNP.

Figure 2. Switching Time Test Circuit

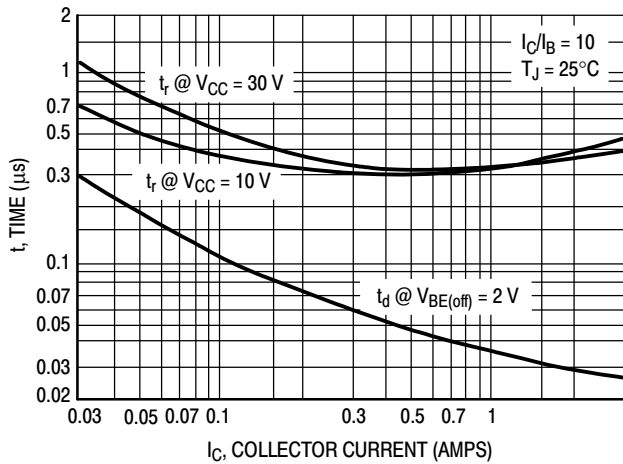


Figure 3. Turn-On Time

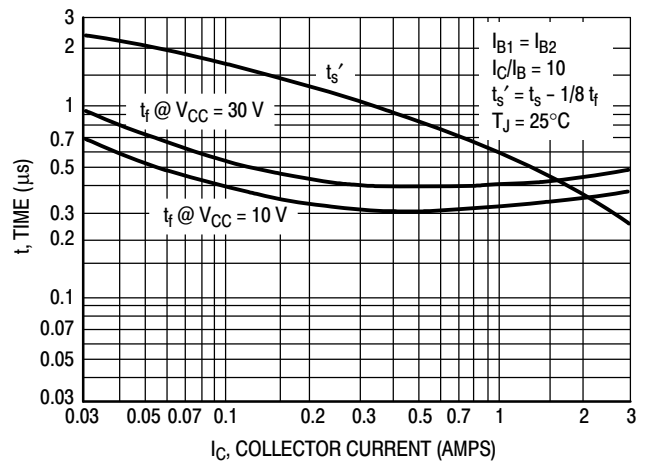


Figure 4. Turn-Off Time

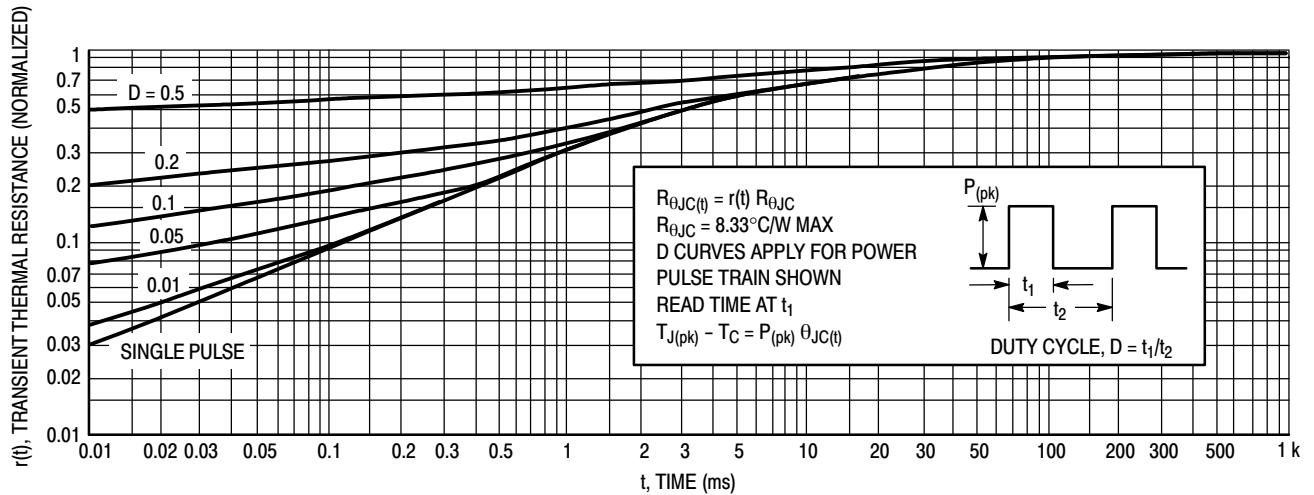


Figure 5. Thermal Response

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)
TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)

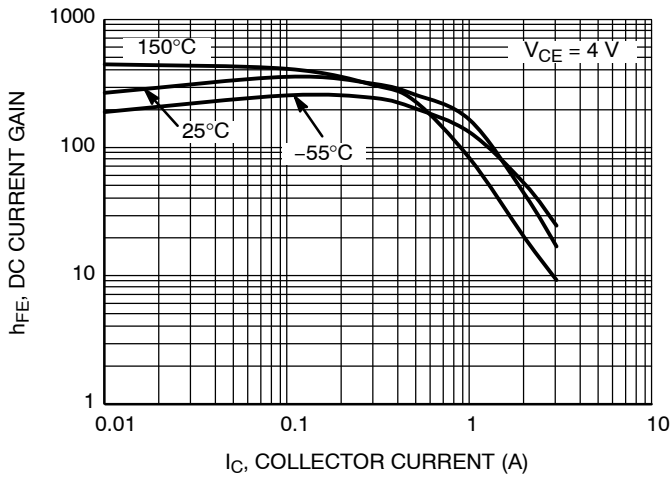


Figure 6. DC Current Gain at $V_{CE} = 4\text{ V}$

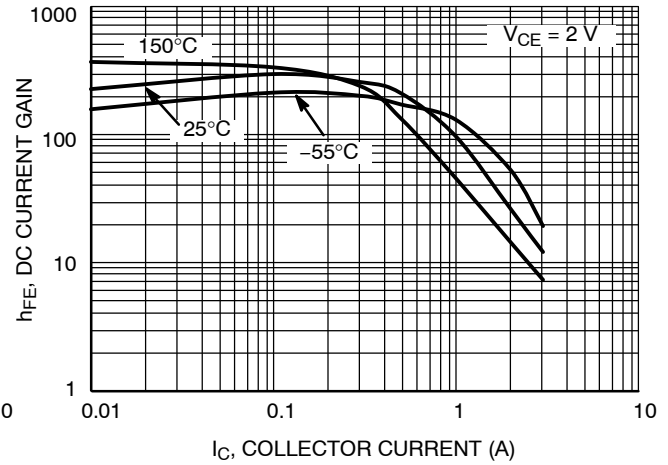


Figure 7. DC Current Gain at $V_{CE} = 2\text{ V}$

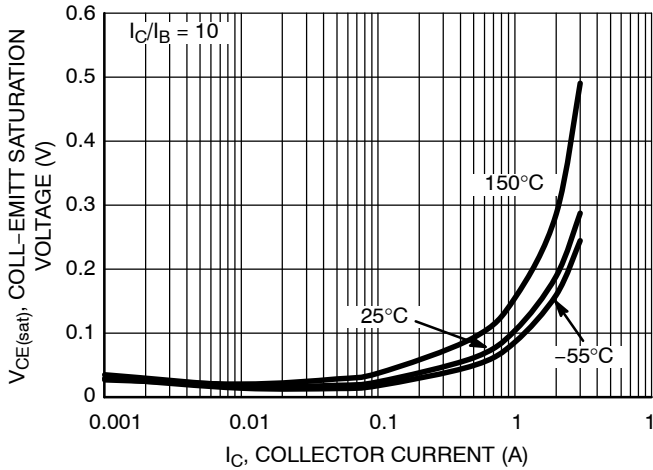


Figure 8. Collector-Emitt Saturation Voltage

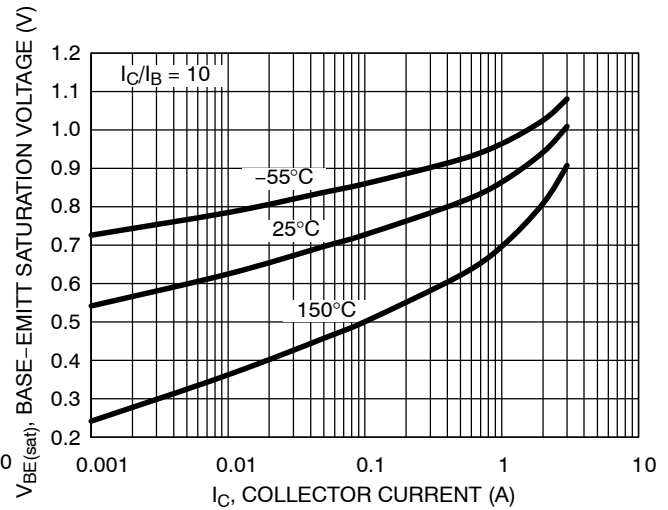


Figure 9. Base-Emitt Saturation Voltage

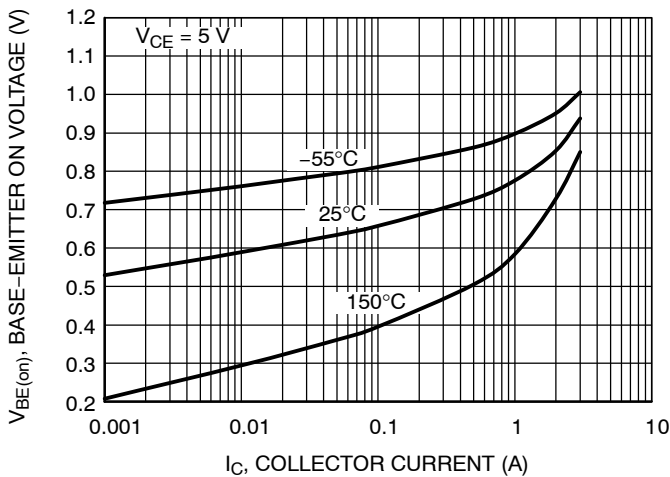


Figure 10. Base-Emitt "On" Voltage

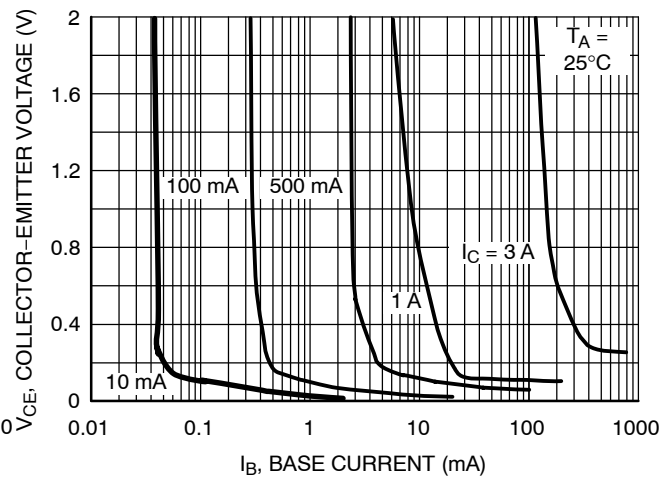


Figure 11. Collector Saturation Region

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)
TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)**

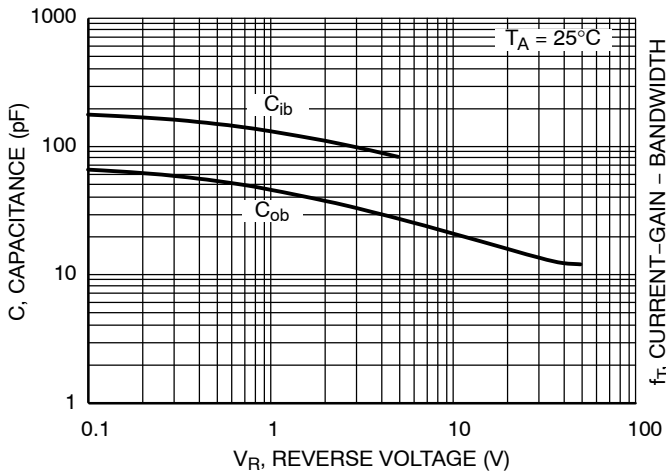


Figure 12. Capacitance

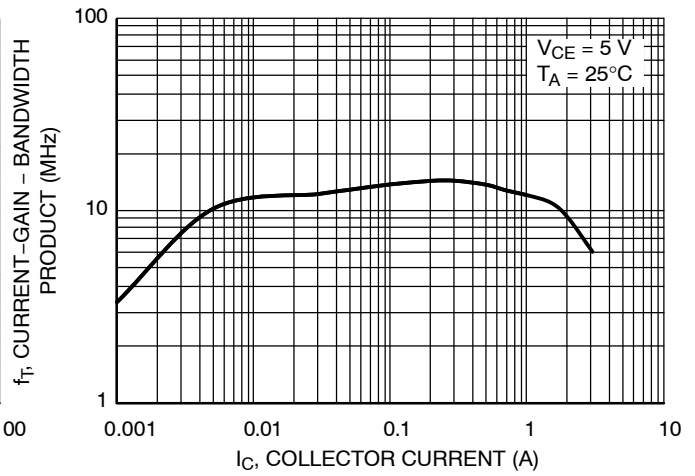


Figure 13. Current-Gain-Bandwidth Product

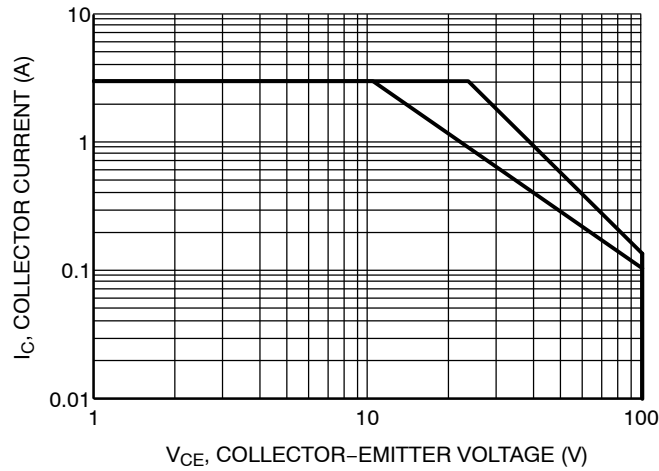


Figure 14. Safe Operating Area

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)
 TYPICAL CHARACTERISTICS – MJD32, MJD32C (PNP)

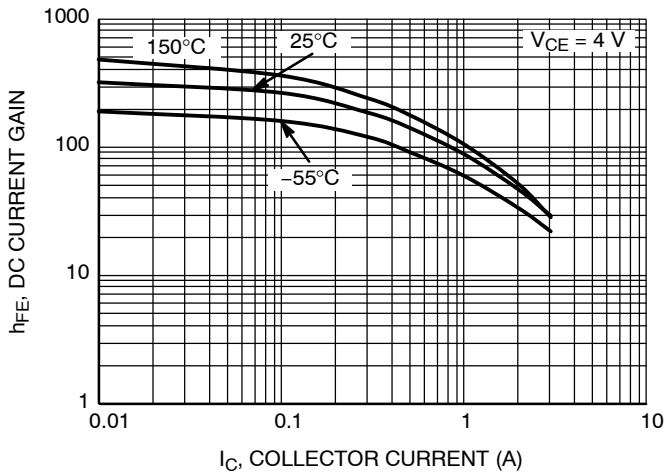


Figure 15. DC Current Gain at $V_{CE} = 4\text{ V}$

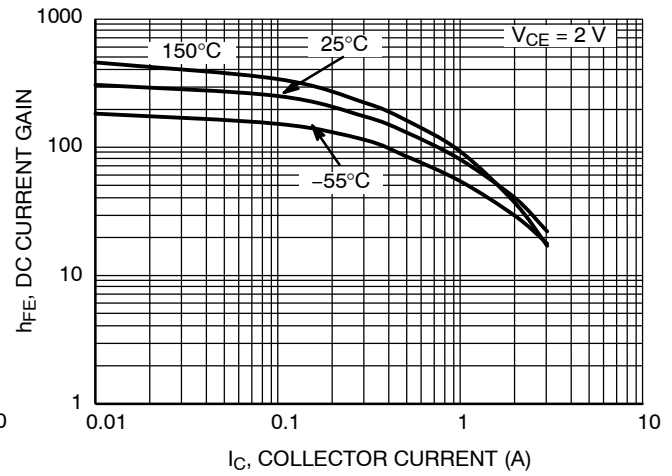


Figure 16. DC Current Gain at $V_{CE} = 2\text{ V}$

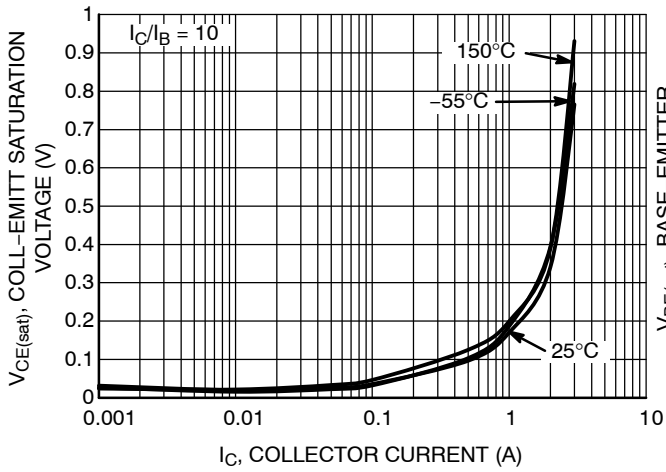


Figure 17. Collector-Emitter Saturation Voltage

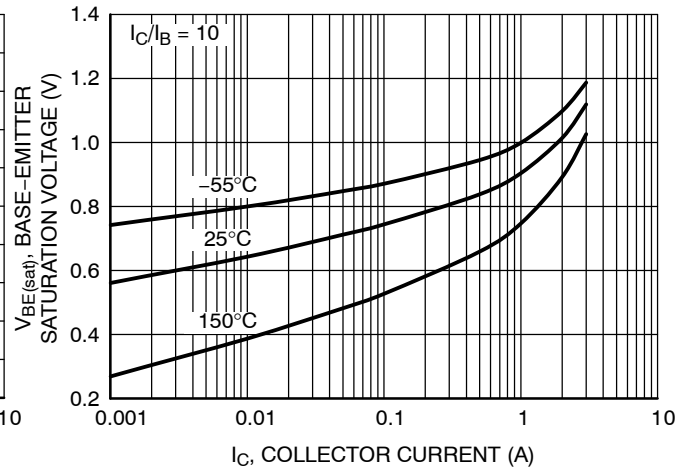


Figure 18. Base-Emitter Saturation Voltage

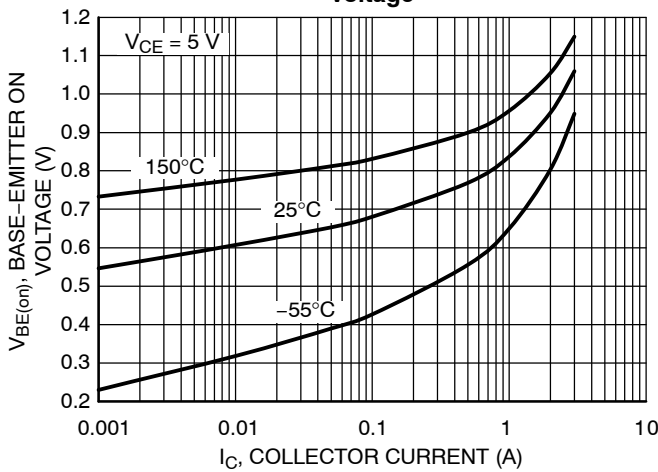


Figure 19. Base-Emitter "On" Voltage

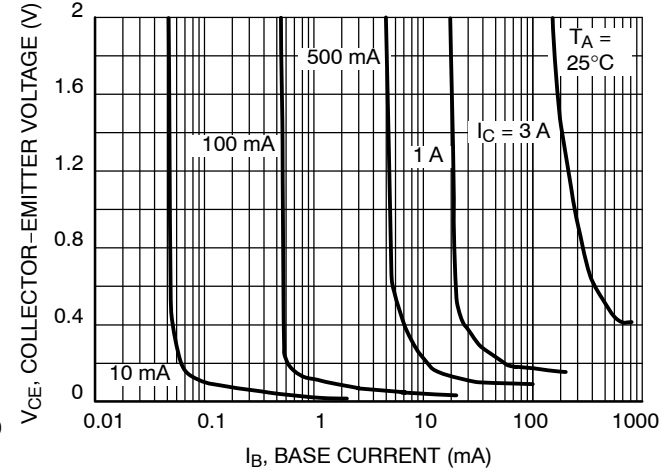


Figure 20. Collector Saturation Region

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS

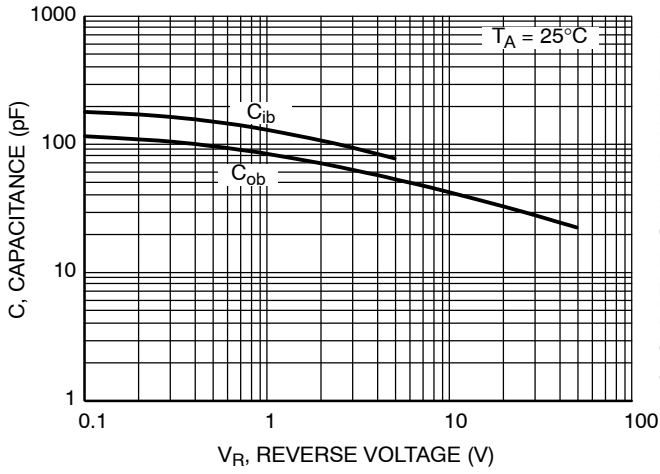


Figure 21. Capacitance

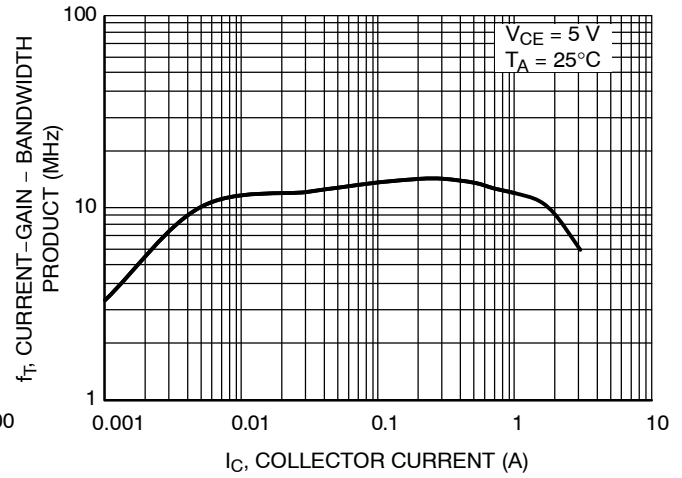


Figure 22. Current-Gain-Bandwidth Product

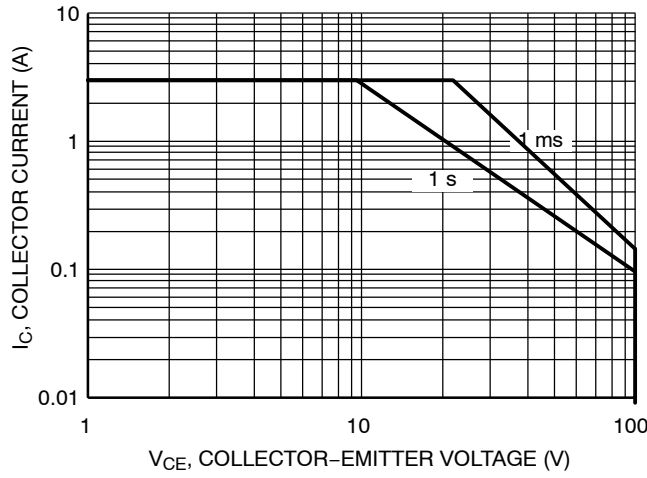


Figure 23. Safe Operating Area

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

ORDERING INFORMATION

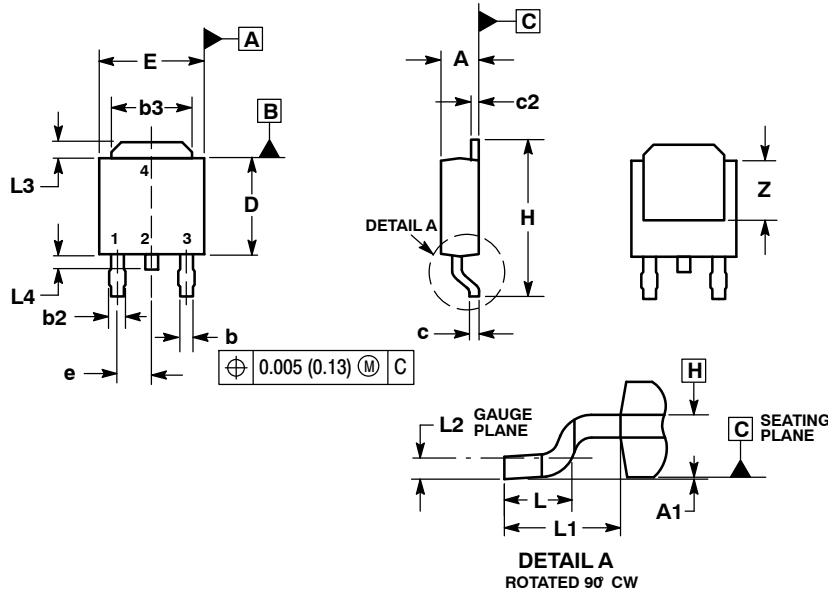
Device	Package Type	Package	Shipping [†]
MJD31CG	DPAK (Pb-Free)	369C	75 Units / Rail
MJD31C1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD31CRLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD31CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD31CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD31T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD31T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD32CG	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD32CG	DPAK (Pb-Free)	369C	75 Units / Rail
MJD32CRLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD32CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD32CT4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD32RLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD32T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD32T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

PACKAGE DIMENSIONS

DPAK
CASE 369C
ISSUE D

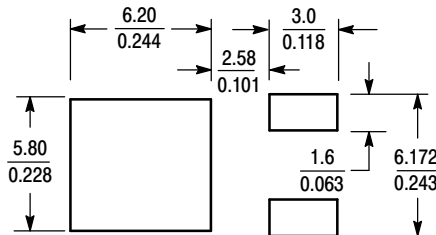


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 ($\frac{\text{mm}}{\text{inches}}$)

STYLE 1:

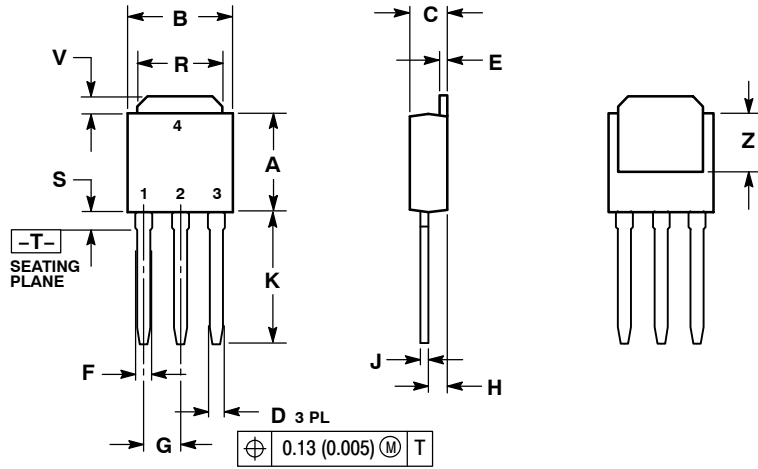
- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

PACKAGE DIMENSIONS

**IPAK
CASE 369D
ISSUE C**



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:

- PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
 Literature Distribution Center for ON Semiconductor
 P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
 USA/Canada
Europe, Middle East and Africa Technical Support:
 Phone: 421 33 790 2910
Japan Customer Focus Center
 Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru